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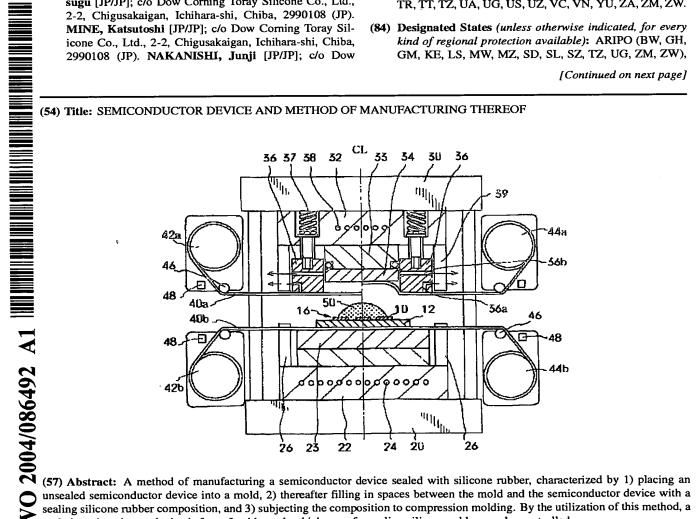
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unsealed semiconductor device into a mold, 2) thereafter filling in spaces between the mold and the semiconductor device with a sealing silicone rubber composition, and 3) subjecting the composition to compression molding. By the utilization of this method, a sealed semiconductor device is free of voids, and a thickness of a sealing silicone rubber can be controlled.